

Silicon PNP Power Transistors

2SA1987

DESCRIPTION

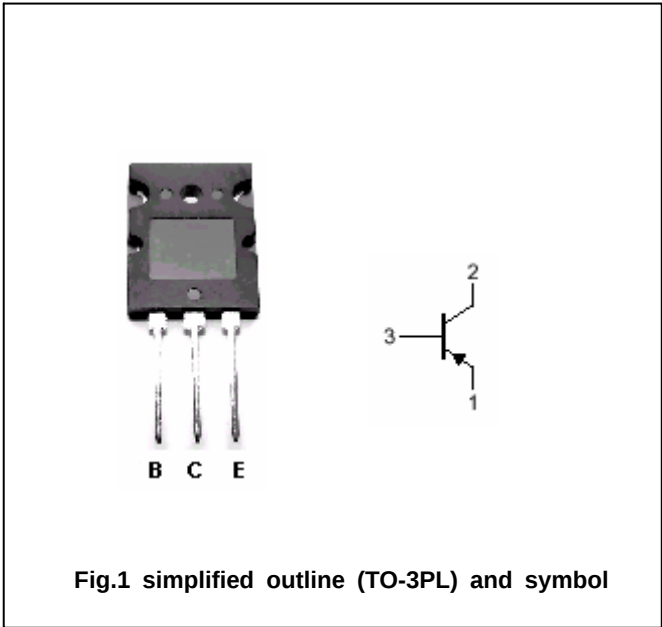
- With TO-3PL package
- Complement to type 2SC5359
- High collector voltage

APPLICATIONS

- Power amplifier applications
- Recommended for 100W high fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-230	V
V _{CEO}	Collector-emitter voltage	Open base	-230	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-15	A
I _B	Base current		-1.5	A
P _C	Collector power dissipation	T _C =25	180	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon PNP Power Transistors

2SA1987

CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -50mA ; I_B = 0$	-230			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -8A ; I_B = -0.8A$		-1.5	-3.0	V
V_{BE}	Base-emitter voltage	$I_C = -7A ; V_{CE} = -5V$		-1.0	-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = -230V ; I_E = 0$			-5	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V ; I_C = 0$			-5	μA
h_{FE-1}	DC current gain	$I_C = -1A ; V_{CE} = -5V$	55		160	
h_{FE-2}	DC current gain	$I_C = -7A ; V_{CE} = -5V$	35			
f_T	Transition frequency	$I_C = -1A ; V_{CE} = -5V$		30		MHz
C_{OB}	Collector output capacitance	$I_E = 0, f = 1MHz ; V_{CB} = -10V$		360		pF

◆ h_{FE-1} classifications

R	O
55-110	80-160

Silicon PNP Power Transistors

2SA1987

PACKAGE OUTLINE

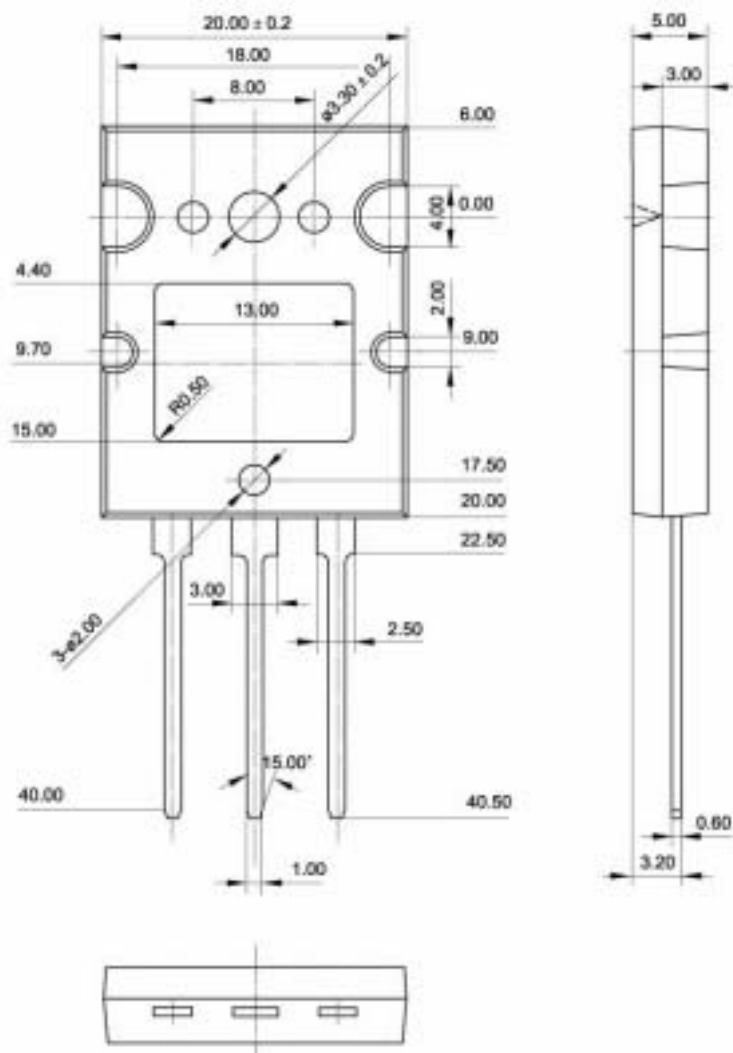


Fig.2 Outline dimensions (unindicated tolerance: ± 0.50 mm)